

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	12	(semiconductor or wafer or substrate) and (coating or coated or coat) and (etching or etch or etched) and (dry adj (clean or cleaning)) and (oxide-based or oxide adj based)	USPAT; US-PGP UB; EPO; JPO	2004/07/16 10:41
2	BRS	L2	3	(semiconductor or wafer or substrate) and (coating or coated or coat) and (etching or etch or etched) and (dry adj (clean or cleaning)) and (oxide-based or oxide adj based) and @pd<20011230	USPAT; US-PGP UB; EPO; JPO	2004/07/16 12:31
3	BRS	L3	3	(semiconductor or wafer or substrate) and (coating or coated or coat) and (etching or etch or etched) and (dry adj (clean or cleaning)) and (oxide-based or oxide adj based) and @pd<20021230	USPAT; US-PGP UB; EPO; JPO	2004/07/16 11:43
4	BRS	L4	54	(semiconductor or wafer or substrate) and (coating or coated or coat) and (etching or etch or etched) and (dry adje (clean or cleaning)) and (oxide or oxide adj based) and (CHF3 or (carbon adj hydroflouride) or "carbon hydroflouride") and @pd<20011230	USPAT; US-PGP UB; EPO; JPO	2004/07/16 12:52
5	BRS	L5	55	(semiconductor or wafer or substrate) and (coating or coated or coat) and (etching or etch or etched) and (dry adje (clean or cleaning)) and (oxide or oxide adj based) and (CHF3 or triflouromethane or "CL.sub2. adj CH.sub3.") and @pd<20011230	USPAT; US-PGP UB; EPO; JPO	2004/07/16 12:55